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June 2014



FQA170N06

N-Channel QFET[®] MOSFET 60 V, 170 A, 5.6 mΩ

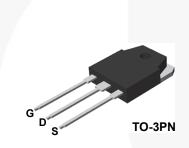
Description

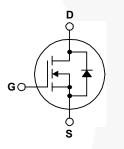
This N-Channel enhancement mode power MOSFET is • 170 A, 60 V, $R_{DS(on)}$ = 5.6 m Ω (Max.) @ V_{GS} = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state . Low Gate Charge (Typ. 220 nC) resistance, and to provide superior switching performance and • Low Crss (Typ. 620 pF) high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor • 100% Avalanche Tested control, and variable switching power applications.

Features

- I_D = 85 A

- 175°C Maximum Junction Temperature Rating





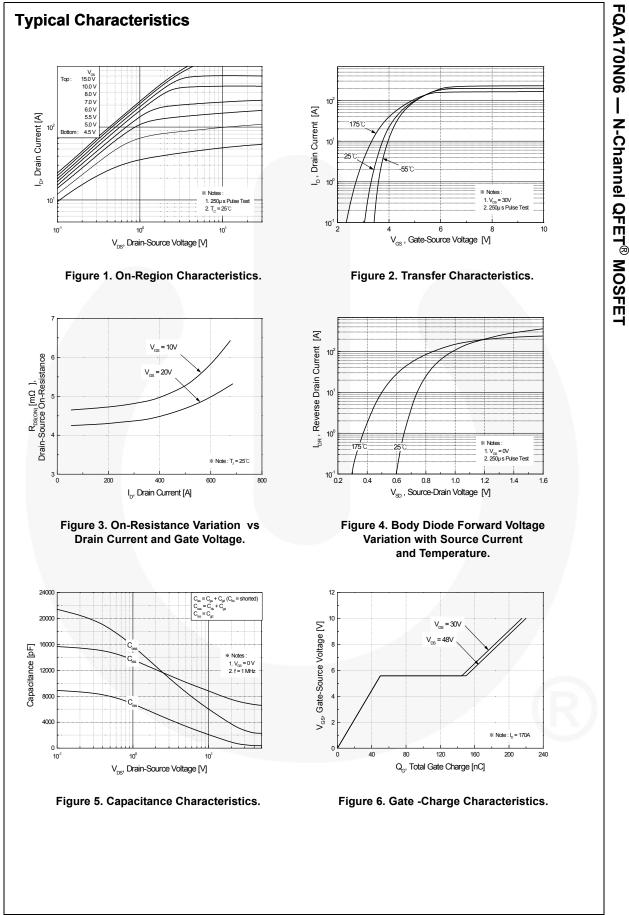
Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

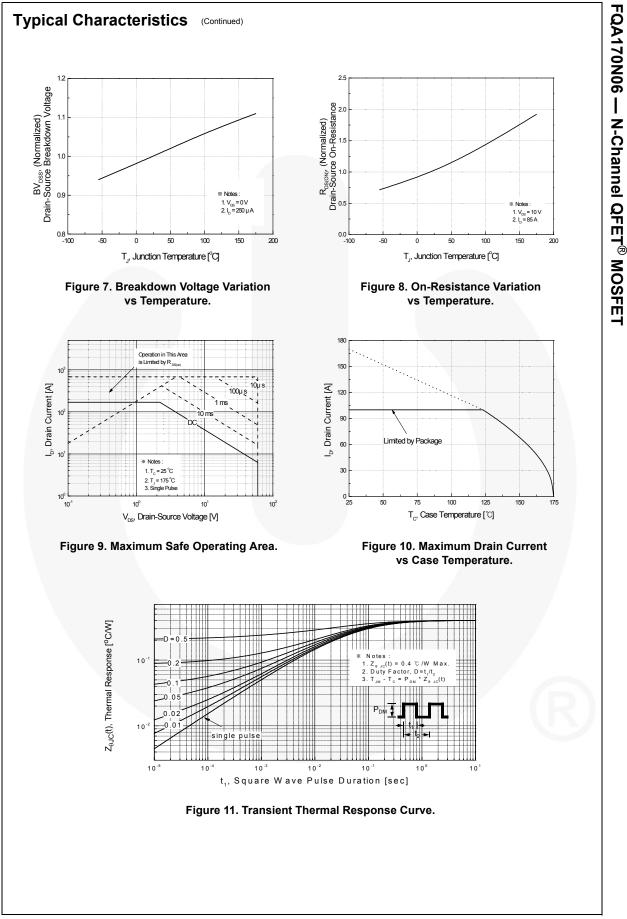
Symbol	Parameter		FQA170N06	Unit
V _{DSS}	Drain-Source Voltage		60	V
I _D	Drain Current - Continuous ($T_C = 25^{\circ}C$)		170	A
	- Continuous (T _C = 100°C)		120	A
I _{DM}	Drain Current - Pulsed	(Note 1)	680	A
V _{GSS}	Gate-Source Voltage		± 25	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	990	mJ
I _{AR}	Avalanche Current	(Note 1)	170	А
E _{AR}	Repetitive Avalanche Energy	(Note 1)	37.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3		7.0	V/ns
P _D	Power Dissipation ($T_C = 25^{\circ}C$)		375	W
	- Derate above 25°C		2.5	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
ΤL	Maximum lead temperature for soldering, 1/8" from case for 5 seconds.		300	°C

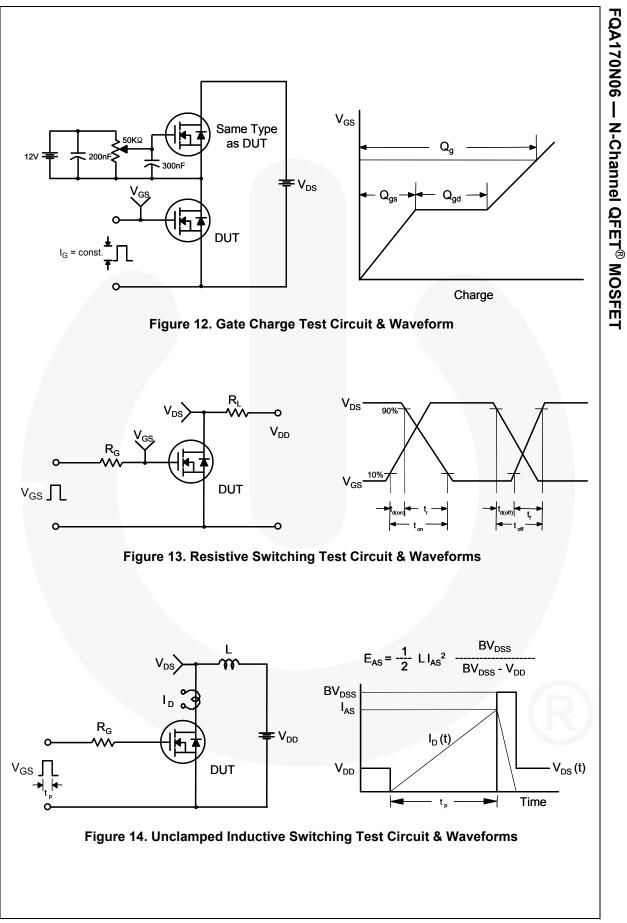
Thermal Characteristics

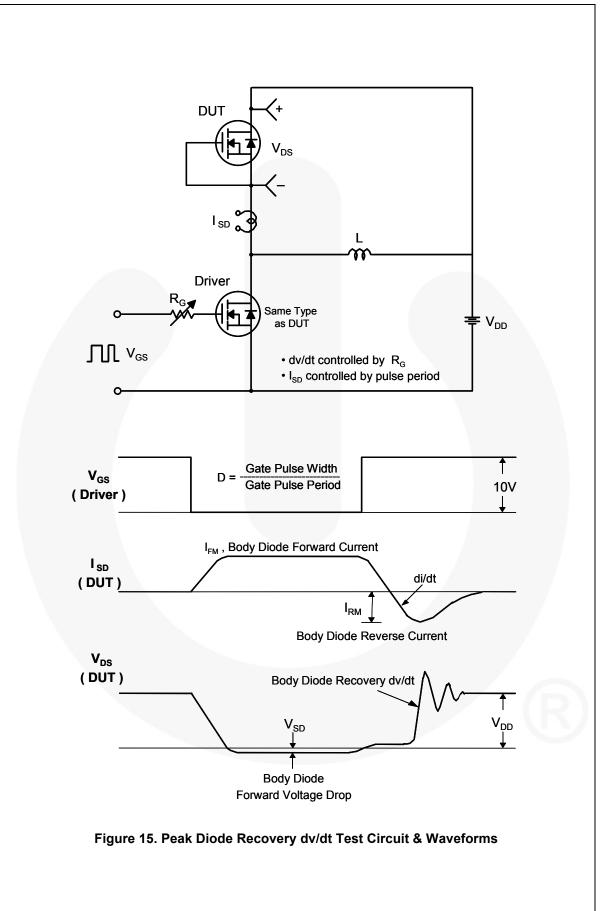
Symbol	Parameter	FQA170N06	Unit	
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	0.4	°C/W	
R_{\thetaJA}	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

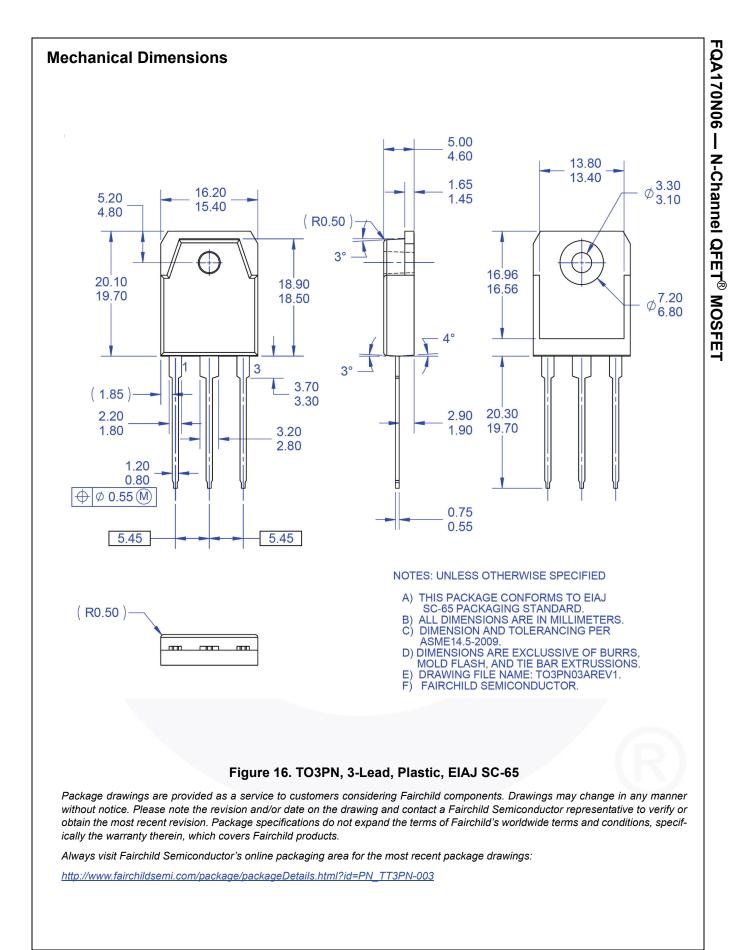
Part	Number	Top Mark	Pac	kage	Packing	Method	Reel	Size	Tape W	idth C	Quantity
FQA170N06		FQA170N06 T0		-3PN Tube		N/A		N/A	\ ;	30 units	
lectri	cal Cha	racteristics	T _C = 25°	C unless otl	herwise noted.						
Symbol		Parameter		Test Conditions				Min.	Тур.	Max.	Unit
Off Cha	aracterist	ics									
BV _{DSS}		rce Breakdown Volta	age	V _{GS} =	0 V, I _D = 25	0 μΑ		60			V
ΔΒV _{DSS} /ΔΤ _J	Breakdown Voltage Temperature Coefficient		$I_D = 250 \ \mu\text{A}$, Referenced to 25°C			25°C		0.053		V/°C	
I _{DSS}	Zero Gate Voltage Drain Current			60 V, V _{GS} =					1	μA	
			V _{DS} = 48 V, T _C = 150°C						10	μA	
I _{GSSF}		Gate-Body Leakage Current, Forward			25 V, V _{DS} =					100	nA
GSSR	Gate-Bod	y Leakage Current, I	Reverse	V _{GS} =	-25 V, V _{DS} :	= 0 V				-100	nA
On Cha	aracterist	ics									
V _{GS(th)}	Gate Thre	shold Voltage		V _{DS} = V	$V_{\rm GS}, {\rm I_{\rm D}} = 2$	50 µA		2.0		4.0	V
R _{DS(on)}	Static Dra On-Resist				10 V, I _D = 8				0.0045	0.0056	Ω
9 _{FS}	Forward T	ransconductance		V _{DS} = 3	30 V, I _D = 8	5 A			85		S
	ic Charac								7200	0250	۶Ę
C _{iss}	Input Cap Output Ca		_	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz		0 V,	-		7200 3100	9350 4000	pF
C _{oss} C _{rss}		ransfer Capacitance	<u>, </u>					620	810	pF pF	
Orss	Reveise i		;						020	810	μr
Switchi	ing Chara	acteristics									
t _{d(on)}	Turn-On D	elay Time		V _{DD} = 30 V, I _D = 85 A,		5 A			85	180	ns
t _r	Turn-On F	Rise Time		00	$R_{\rm G} = 25 \Omega$				700	1400	ns
t _{d(off)}	Turn-Off D	elay Time							260	530	ns
t _f	Turn-Off F	all Time				(N	lote 4)		430	870	ns
Qg	Total Gate	Charge		V _{DS} = 48 V, I _D = 170 A,		70 A,			220	290	nC
Q _{gs}	Gate-Sou	rce Charge			V _{GS} = 10 V				50		nC
Q _{gd}	Gate-Drai	n Charge				(N	Note 4)		100		nC
	1	ode Characteri				<u> </u>	1				
I _S			ource Diode Forward Current (Note			Note 5)			170	A	
I _{SM}				e Diode Forward Current						680	A
V _{SD}		rce Diode Forward	/oltage	$V_{GS} = 0 V, I_S = 170 A$					1.5	V	
		Recovery Time Recovery Charge		V _{GS} = 0 V, I _S = 170 A, dI _F / dt = 100 A/µs					100		ns
t _{rr} Q _{rr}				$-\alpha = /\alpha t$	= 100 A/08				315	(nC













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